2-Bit 20 Mb/s Dual-Supply Level Translator

NLSX0102

The NLSX0102 is a 2−bit configurable dual−supply bidirectional auto sensing translator that does not require a directional control pin. The I/O V_{CC} and I/O V_L ports are designed to track two different power supply rails, V_{CC} and V_L respectively. Both the V_{CC} and V_L supply rails are configurable from 1.65 V to 5.5 V. This allows voltage logic signals on the V_L side to be translated into voltage logic signals on the V_{CC} side, and vice−versa.

The NLSX0102 translator has integrated 10 kΩ pull−up resistors on the I/O lines. The integrated pull−up resistors are used to pull−up the I/O lines to either V_L or V_{CC}. The NLSX0102 is an excellent match for open−drain applications such as the I^2C communication bus.

Features

- Wide V_{CC} Operating Range: V_L to 5.5 V
  Wide V_L Operating Range: 1.65 V to 5.5 V
- High−Speed with 24 Mb/s Guaranteed Date Rate
- Low Bit−to−Bit Skew
- Enable Input and I/O Pins are
  Overvoltage Tolerant (OVT) to 5.5 V
- Non−preferential Power−up Sequencing
- Integrated 10 kΩ Pull−up Resistors
- Small Space Saving Package
  – 1.9 mm x 0.9 mm x 0.5 mm Flipchip8
- This is a Pb−Free Device

Typical Applications

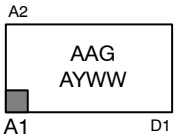
- I^2C, SMBus
- Low Voltage ASIC Level Translation
- Mobile Phones, PDAs, Cameras

Important Information

- ESD Protection for All Pins
  – Human Body Model (HBM) > 7000 V

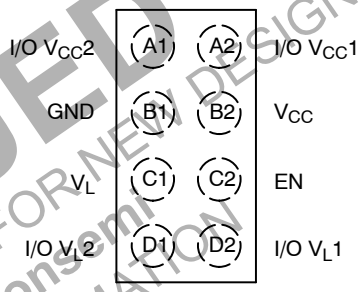
FLIP−CHIP 8
CASE 499BF

MARKING DIAGRAM



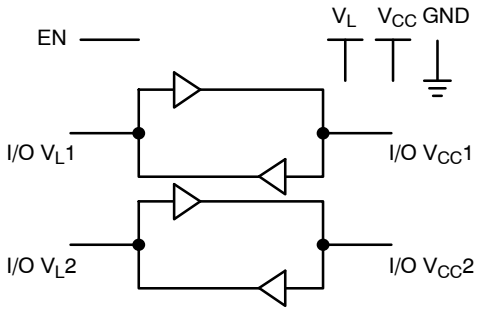
AAG	= Specific Device Code
A	= Assembly Location
Y	= Year
WW	= Work Week

PIN ASSIGNMENTS



(Top View)

LOGIC DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

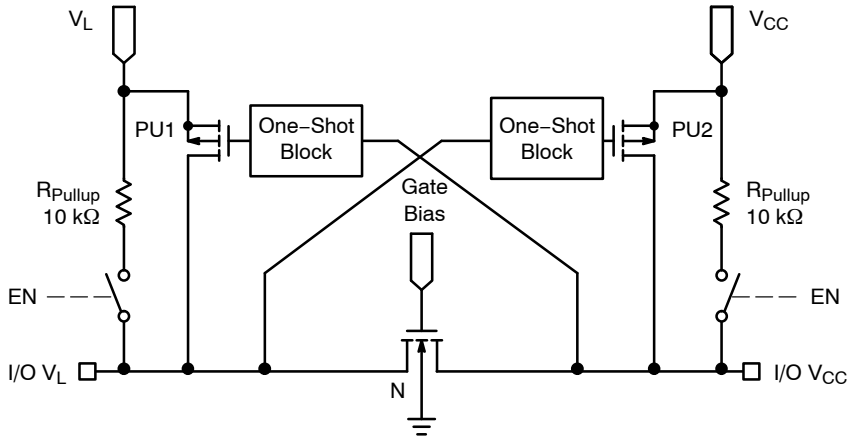


Figure 1. Block Diagram (1 I/O Line)

PIN ASSIGNMENT

Pins	Description
V_{CC}	V_{CC} Supply Voltage
V_L	V_L Supply Voltage
GND	Ground
EN	Output Enable, referenced to V_L
I/O V_{CC}n	I/O Port, referenced to V_{CC}
I/O V_Ln	I/O Port, referenced to V_L

FUNCTION TABLE

EN	Operating Mode
L	Hi−Z
H	I/O Buses Connected

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V_{CC}	High−side DC Supply Voltage	−0.5 to +7.0		V
V_L	Low−side DC Supply Voltage	−0.5 to +7.0		V
I/O V_{CC}	V_{CC}−referenced DC Input / Output Voltage	−0.5 to +7.0		V
I/O V_L	V_L−referenced DC Input / Output Voltage	−0.5 to +7.0		V
V_{EN}	Enable Control Pin DC Input Voltage	−0.5 to +7.0		V
I_{I/O_SC}	Short−Circuit Duration (I/O V_L and I/O V_{CC} to GND)	±50	Continuous	mA
$I_{I/OK}$	Input / Output Clamping Current (I/O V_L and I/O V_{CC})	−50	$V_{I/O}$ < 0	mA
T_{STG}	Storage Temperature	−65 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	High−side Positive DC Supply Voltage	V_L	5.5	V
V_L	Low−side Positive DC Supply Voltage	1.65	5.5	V
V_{EN}	Enable Control Pin Voltage	GND	5.5	V
V_{IO}	I/O Pin Voltage	GND	5.5	V
$\Delta t/\Delta V$	Input Transition Rise and Fall Rate I/O V_L and I/O V_{CC} Ports, Push−Pull Driving		10	ns/V
	Control Input		10	
T_A	Operating Temperature Range	−40	+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (T_A = −40 to +85 °C, unless otherwise specified)

Symbol	Parameter	Test Conditions (Note 1)	V_L	V_{CC}	−40 °C to +85°C			Unit
					Min	Typ (Notes 1, 2)	Max	
V_{IHC}	I/O V_{CC} Input HIGH Voltage		1.65 to 5.5	V_L to 5.5	V_{CC} – 0.4		–	V
V_{ILC}	I/O V_{CC} Input LOW Voltage		1.65 to 5.5	V_L to 5.5			0.15	V
V_{IHL}	I/O V_L Input HIGH Voltage		1.65 to 5.5	V_L to 5.5	V_L – 0.4		–	V
V_{ILL}	I/O V_L Input LOW Voltage		1.65 to 5.5	V_L to 5.5			0.15	V
V_{IH}	Control Pin Input HIGH Voltage		1.65 to 5.5	V_L to 5.5	0.75 * V_L		–	V
V_{IL}	Control Pin Input LOW Voltage		1.65 to 5.5	V_L to 5.5			0.25 * V_L	V
V_{OHC}	I/O V_{CC} Output HIGH Voltage	I/O V_{CC} source current = −20 μA	1.65 to 5.5	V_L to 5.5	2/3 * V_{CC}		–	V
V_{OLC}	I/O V_{CC} Output LOW Voltage	I/O V_{CC} sink current = 1 mA	1.65 to 5.5	V_L to 5.5			0.4	V
V_{OHL}	I/O V_L Output HIGH Voltage	I/O V_L source current = −20 μA	1.65 to 5.5	V_L to 5.5	2/3 * V_L		–	V
V_{OLL}	I/O V_L Output LOW Voltage	I/O V_L sink current = 1 mA	1.65 to 5.5	V_L to 5.5			0.4	V
I_{QVL}	V_L Supply Current Supply Current	I/O V_{CC} and I/O V_L unconnected, V_{EN} = V_L	1.65 to 5.5	V_L to 5.5			2.4	μA
			5.5	0			2.4	
I_{QVCC}	V_L Supply Current Supply Current	I/O V_{CC} and I/O V_L unconnected, V_{EN} = V_L	1.65 to 5.5	V_L to 5.5			2.4	μA
			0	5.5			2.4	
I_{TS-VCC}	V_{CC} Tri−state Output Mode	I/O V_{CC} and I/O V_L unconnected, V_{EN} = GND	1.65 to 5.5	V_L to 5.5			1.0	μA
I_{TS-VL}	V_L Tri−state Output Mode Supply Current	I/O V_{CC} and I/O V_L unconnected, V_{EN} = GND	1.65 to 5.5	V_L to 5.5			1.0	μA
I_I	Enable Pin Input Leakage Current		1.65 to 5.5	V_L to 5.5			1.0	μA
I_{OZ}	I/O Tri−state Output Mode Leakage Current		1.65 to 5.5	V_L to 5.5			1.0	μA
R_{PU}	Pull−Up Resistors I/O V_L and V_C					10		kΩ

1. Typical values are for V_{CC} = +3.3 V, V_L = +1.8 V and T_A = +25°C.
2. All units are production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Timing Characteristics – Rail−to−Rail Driving Configuration

(I/O test circuits of Figures 2, 3 and 7, C_{LOAD} = 15 pF, driver output impedance ≤ 50 Ω, R_{LOAD} = 1 MΩ, unless otherwise specified)

Symbol	Parameter	Conditions	−40°C to +85°C						Unit
			V_{CC} = 2.3 to 2.7 V		V_{CC} = 3.0 to 3.6 V		V_{CC} = 4.5 to 5.5 V		
			Min	Max	Min	Max	Min	Max	
V_L = 1.65 to 1.95 V									
t_{RVL}	I/O V_L Rise Time	Figure 8	0.6	17.0	2.3	14.0	0.8	12.9	nS
t_{RVCC}	I/O V_{CC} Rise Time	Figure 8	4.0	10.8	2.2	9.1	2.7	7.6	nS
t_{FVL}	I/O V_L Fall Time	Figure 8	2.0	9.7	1.9	8.1	1.7	13.3	nS
t_{FVCC}	I/O V_{CC} Fall Time	Figure 8	2.9	13.8	2.8	16.2	2.8	16.2	nS
$t_{PHL-VL-VCC}$	Propagation Delay (Driving I/O V_L, V_L to V_{CC})	Figure 2		7.2		7.1		10.0	nS
$t_{PLH-VL-VCC}$				6.5		7.1		7.4	
$t_{PHL-VCC-VL}$	Propagation Delay (Driving I/O V_{CC}, V_{CC} to V_L)	Figure 3		6.0		5.3		6.7	nS
$t_{PLH-VCC-VL}$				8.0		7.6		7.1	
t_{EN}	Enable Time	Figure 7		50		40		35	nS
t_{DIS}	Disable Time	Figure 7		390		365		710	nS
t_{PPSKEW}	Part−to−Part Skew			0.7		0.7		0.7	nS
MDR	Maximum Data Rate		21		22		24		Mbps
V_L = 2.3 to 2.7 V									
t_{RVL}	I/O V_L Rise Time	Figure 8	2.8	8.6	2.6	8.1	1.8	10.3	nS
t_{RVCC}	I/O V_{CC} Rise Time	Figure 8	3.2	9.2	2.9	8.8	1.9	7.7	nS
t_{FVL}	I/O V_L Fall Time	Figure 8	1.9	8.3	1.9	7.8	1.8	7.4	nS
t_{FVCC}	I/O V_{CC} Fall Time	Figure 8	2.2	8.3	2.4	8.0	2.6	10.0	nS
$t_{PHL-VL-VCC}$	Propagation Delay (Driving I/O V_L, V_L to V_{CC})	Figure 2		4.8		5.2		6.5	nS
$t_{PLH-VL-VCC}$				5.4		5.3		6.0	
$t_{PHL-VCC-VL}$	Propagation Delay (Driving I/O V_{CC}, V_{CC} to V_L)	Figure 3		5.0		3.9		5.4	nS
$t_{PLH-VCC-VL}$				5.5		5.0		5.5	
t_{EN}	Enable Time	Figure 7		100		40		35	nS
t_{DIS}	Disable Time	Figure 7		320		305		430	nS
t_{PPSKEW}	Part−to−Part Skew			0.7		0.7		0.7	nS
MDR	Maximum Data Rate		20		22		24		Mbps

Timing Characteristics – Rail−to−Rail Driving Configuration

(I/O test circuits of Figures 2, 3 and 7, C_{LOAD} = 15 pF, driver output impedance ≤ 50 Ω, R_{LOAD} = 1 MΩ, unless otherwise specified)

Symbol	Parameter	Conditions	−40°C to +85°C						Unit
			V_{CC} = 2.3 to 2.7 V		V_{CC} = 3.0 to 3.6 V		V_{CC} = 4.5 to 5.5 V		
			Min	Max	Min	Max	Min	Max	
V_L = 3.0 to 3.6 V									
t_{RVL}	I/O V_L Rise Time	Figure 8			2.3	6.5	1.9	8.0	nS
t_{RVCC}	I/O V_{CC} Rise Time	Figure 8			2.5	6.5	2.1	7.4	nS
t_{FVL}	I/O V_L Fall Time	Figure 8			1.3	7.2	1.6	11.0	nS
t_{FVCC}	I/O V_{CC} Fall Time	Figure 8			1.7	8.0	1.3	9.3	nS
$t_{PHL−VL−VCC}$	Propagation Delay (Driving I/O V_L, V_L to V_{CC})	Figure 2				3.9		4.6	nS
$t_{PLH−VL−VCC}$						3.8		3.8	
$t_{PHL−VCC−VL}$	Propagation Delay (Driving I/O V_{CC}, V_{CC} to V_L)	Figure 3				3.8		4.6	nS
$t_{PLH−VCC−VL}$						4.3		5.8	
t_{EN}	Enable Time	Figure 7				80		35	nS
t_{DIS}	Disable Time	Figure 7				260		385	nS
t_{PPSKEW}	Part−to−Part Skew					0.7		0.7	nS
MDR	Maximum Data Rate				23		24		Mbps

Timing Characteristics – Open Drain Driving Configuration

(I/O test circuits of Figures 4, 5 and 7, C_{LOAD} = 15 pF, driver output impedance ≤ 50 Ω, R_{LOAD} = 1 MΩ, unless otherwise specified)

Symbol	Parameter	Conditions	−40°C to +85°C						Unit
			V_{CC} = 2.3 to 2.7 V		V_{CC} = 3.0 to 3.6 V		V_{CC} = 4.5 to 5.5 V		
			Min	Max	Min	Max	Min	Max	
V_L = 1.65 to 1.95 V									
t_{RVL}	I/O V_L Rise Time	Figure 8	38	340	30	245	22.0	134	nS
t_{RVCC}	I/O V_{CC} Rise Time	Figure 8	34	330	23	218	10.0	120	nS
t_{FVL}	I/O V_L Fall Time	Figure 8	4.4	11.1	4.3	12.0	4.2	14.2	nS
t_{FVCC}	I/O V_{CC} Fall Time	Figure 8	6.9	11	7.5	16.2	7.0	16.2	nS
$t_{PHLVL−VCC}$	Propagation Delay (Driving I/O V_L, V_L to V_{CC})	Figure 2	2.3	27	2.4	20.0	2.6	23.0	nS
$t_{PLHVL−VCC}$			45	260	36.0	208	27.0	208	
$t_{PHLVCC−VL}$	Propagation Delay (Driving I/O V_{CC}, V_{CC} to V_L)	Figure 3	1.9	22	1.1	22.0	1.2	22.0	nS
$t_{PLHVCC−VL}$			45.0	200	36	150	27.0	112	
t_{EN}	Enable Time	Figure 7		80		70		35	nS
t_{DIS}	Disable Time	Figure 7		250		277		290	nS
t_{PPSKEW}	Part−to−Part Skew			0.7		0.7		0.7	nS
MDR	Maximum Data Rate		2		2		2		Mbps

Timing Characteristics – Open Drain Driving Configuration

(I/O test circuits of Figures 4, 5 and 7, C_{LOAD} = 15 pF, driver output impedance ≤ 50 Ω, R_{LOAD} = 1 MΩ, unless otherwise specified)

Symbol	Parameter	Conditions	–40°C to +85°C						Unit
			V_{CC} = 2.3 to 2.7 V		V_{CC} = 3.0 to 3.6 V		V_{CC} = 4.5 to 5.5 V		
			Min	Max	Min	Max	Min	Max	
V_L = 2.3 to 2.7 V									
t_{RVL}	I/O V_L Rise Time	Figure 8	34	400	28.0	300	24.0	208	nS
t_{RVCC}	I/O V_{CC} Rise Time	Figure 8	35.0	352	24.0	280	12.0	180	nS
t_{FVL}	I/O V_L Fall Time	Figure 8	4.4	6.9	4.3	6.2	4.2	7.8	nS
t_{FVCC}	I/O V_{CC} Fall Time	Figure 8	4.3	8.8	4.9	9.4	5.4	10.4	nS
$t_{PHLVL-VCC}$	Propagation Delay (V_L to V_{CC})	Figure 2	1.7	14.0	2.0	14.0	2.1	14.0	nS
$t_{PLHVL-VCC}$			43.0	250	36.0	210	27.0	210	
$t_{PHLVCC-VL}$	Propagation Delay (V_{CC} to V_L)	Figure 3	1.8	13.0	2.6	13.0	1.2	13.0	nS
$t_{PLHVCC-VL}$			44.0	225	37.0	180	27.0	144	
t_{EN}	Enable Time	Figure 7		50		40		35	nS
t_{DIS}	Disable Time	Figure 7		265		230		215	nS
t_{PPSKEW}	Part–to–Part Skew			0.7		0.7		0.7	nS
MDR	Maximum Data Rate		2		2		2		Mbps
V_L = 3.0 to 3.6 V									
t_{RVL}	I/O V_L Rise Time	Figure 8			25.0	400	19.0	278	nS
t_{RVCC}	I/O V_{CC} Rise Time	Figure 8			26.0	375	14.0	247	nS
t_{FVL}	I/O V_L Fall Time	Figure 8			2.8	6.1	2.6	5.7	nS
t_{FVCC}	I/O V_{CC} Fall Time	Figure 8			2.6	7.6	3.1	8.3	nS
$t_{PHLVL-VCC}$	Propagation Delay (V_L to V_{CC})	Figure 2			1.3	10.0	1.4	8.0	nS
$t_{PLHVL-VCC}$					36.0	255	28.0	243	
$t_{PHLVCC-VL}$	Propagation Delay (V_{CC} to V_L)	Figure 3			1.0	124	1.0	97.0	nS
$t_{PLHVCC-VL}$					3.0	185	3.0	136	
t_{EN}	Enable Time	Figure 7				40		35	nS
t_{DIS}	Disable Time	Figure 7				250		205	nS
t_{PPSKEW}	Part–to–Part Skew					0.7		0.7	nS
MDR	Maximum Data Rate				2		2		Mbps

TEST SETUPS

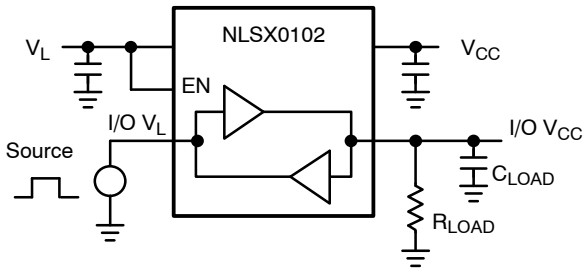


Figure 2. Rail−to−Rail Driving I/O V_L

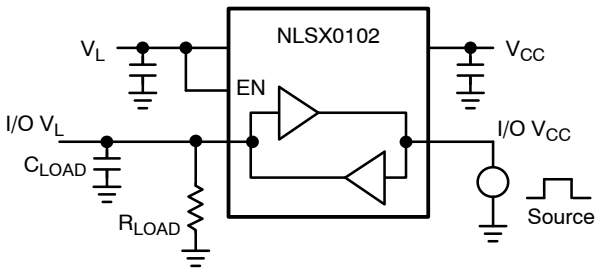


Figure 3. Rail−to−Rail Driving I/O V_{CC}

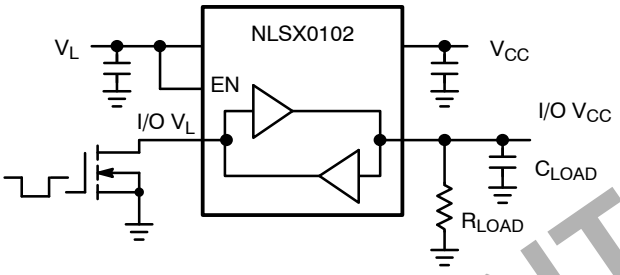


Figure 4. Open−Drain Driving I/O V_L

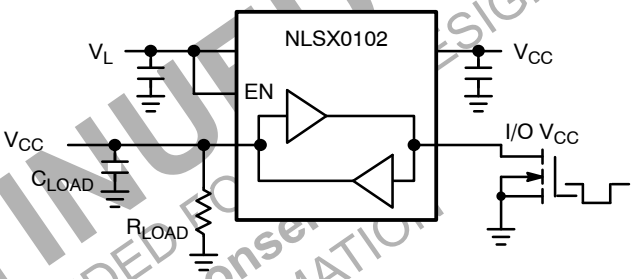


Figure 5. Open−Drain Driving I/O V_{CC}

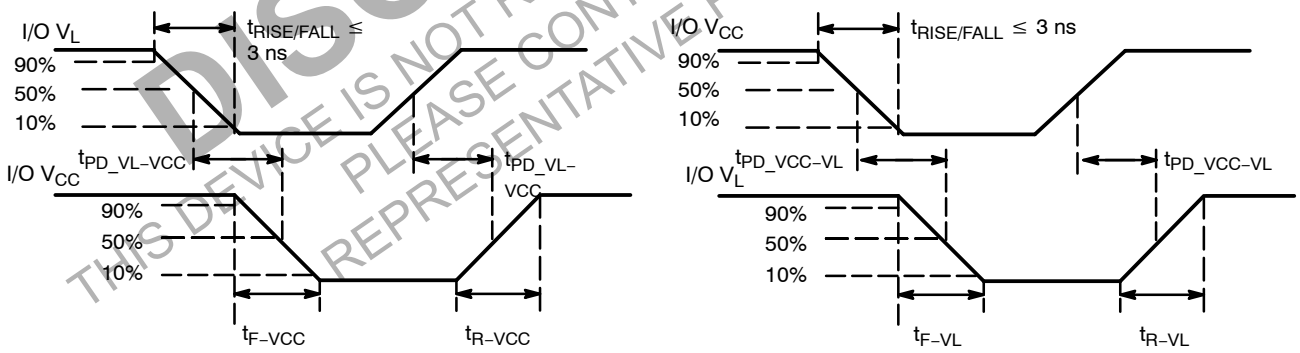
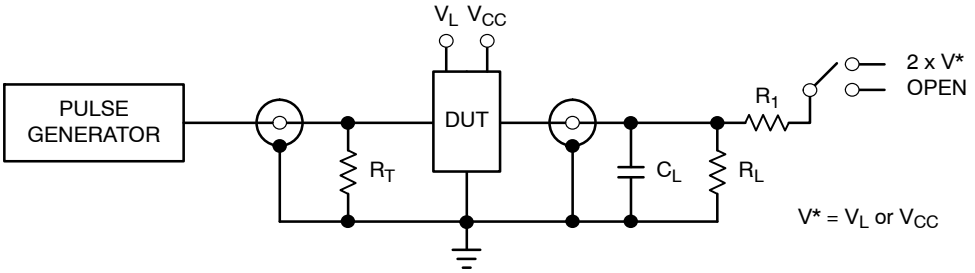


Figure 6. Definition of Timing Specification Parameters



Test	Switch
t_{PZH}, t_{PHZ}	Open
t_{PZL}, t_{PLZ}	2 x V*

C_L = 15 pF or equivalent (Includes jig and probe capacitance)
R_L = R_1 = 50 kΩ or equivalent
R_T = Z_{OUT} of pulse generator (typically 50 Ω)
V* = V_L or V_{CC} for I/O_VL or I/O_VCC measurements, respectively.

Figure 7. Test Circuit for Enable/Disable Time Measurement

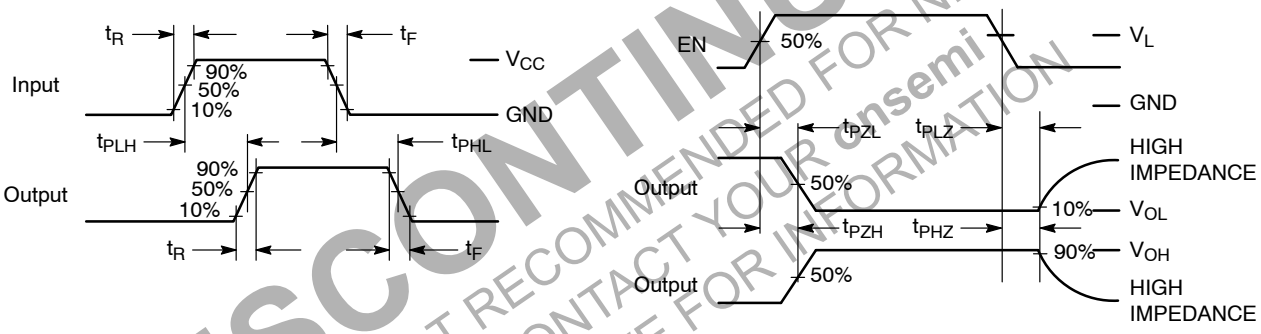


Figure 8. Timing Definitions for Propagation Delays and Enable/Disable Measurement

APPLICATIONS INFORMATION

Level Translator Architecture

The NLSX0102 auto sense translator provides bi−directional voltage level shifting to transfer data in multiple supply voltage systems. This device has two supply voltages, V_L and V_{CC}, which set the logic levels on the input and output sides of the translator. When used to transfer data from the V_L to the V_{CC} ports, input signals referenced to the V_L supply are translated to output signals with a logic level matched to V_{CC}. In a similar manner, the V_{CC} to V_L translation shifts input signals with a logic level compatible to V_{CC} to an output signal matched to V_L.

The NLSX0102 consists of two bi−directional channels that independently determine the direction of the data flow without requiring a directional pin. The one−shot circuits are used to detect the rising or falling input signals. In addition, the one shots decrease the rise and fall time of the output signal for high−to−low and low−to−high transitions. Each input/output channel has an internal 10 kΩ pull−up. The magnitude of the pull−up resistors can be reduced by connecting external resistors in parallel to the internal 10 kΩ resistors.

Input Driver Requirements

The rise (t_R) and fall (t_F) timing parameters of the open drain outputs depend on the magnitude of the pull−up resistors. In addition, the propagation times (t_{PD}), skew (t_{PSKEW}) and maximum data rate depend on the impedance of the device that is connected to the translator. The timing parameters listed in the data sheet assume that the output impedance of the drivers connected to the translator is less than 50 kΩ.

Enable Input (EN)

The NLSX0102 has an Enable pin (EN) that provides tri−state operation at the I/O pins. Driving the Enable pin to a low logic level minimizes the power consumption of the device and drives the I/O V_{CC} and I/O V_L pins to a high impedance state. Normal translation operation occurs when the EN pin is equal to a logic high signal. The EN pin is referenced to the V_L supply and has Overvoltage Tolerant (OVT) protection.

Power Supply Guidelines

During normal operation, supply voltage V_L must be less than or equal to V_{CC}. The sequencing of the power supplies will not damage the device during the power up operation. For optimal performance, 0.01 μF to 0.1 μF decoupling capacitors should be used on the V_L and V_{CC} power supply pins. Ceramic capacitors are a good design choice to filter and bypass any noise signals on the voltage lines to the ground plane of the PCB. The noise immunity will be maximized by placing the capacitors as close as possible to the supply and ground pins, along with minimizing the PCB connection traces.

ORDERING INFORMATION

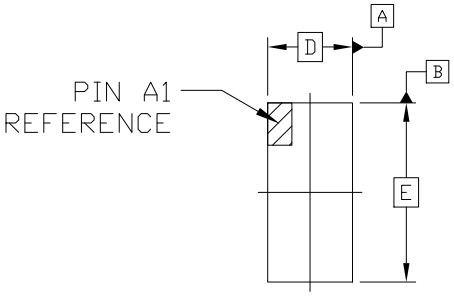
Device	Package	Shipping†
NLSX0102FCT1G	Flip−Chip 8 (Pb−Free)	3000 / Tape & Reel
NLSX0102FCT2G	Flip−Chip 8 (Pb−Free)	3000 / Tape & Reel (4mm Pitch Carrier Tape)
NLSX0102FC2T2G	Flip−Chip 8 (Pb−Free)	3000 / Tape & Reel (2mm Pitch Carrier Tape)

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

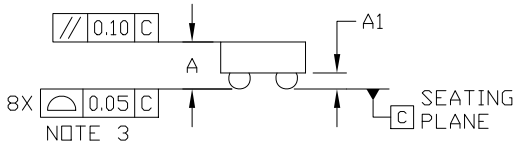
8 PIN FLIP−CHIP, 0.9x1.9, 0.5P
CASE 499BF
ISSUE A

SCALE 4:1

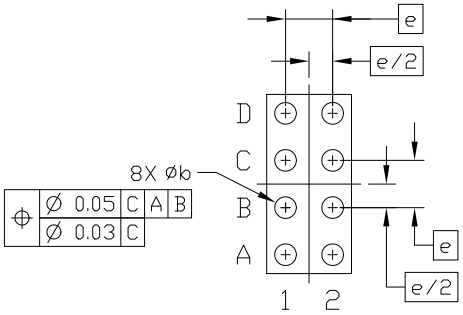
DATE 12 JAN 2022



TOP VIEW



SIDE VIEW

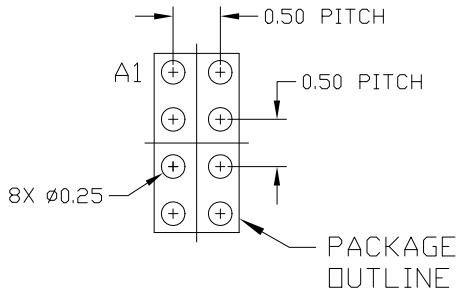


BOTTOM VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE SPHERICAL CROWNS OF THE SOLDER BALLS.

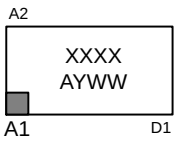
DIM	MILLIMETERS	
	MIN	MAX
A	0.44	0.50
A1	0.18	0.22
b	0.24	0.28
D	0.90 BSC	
E	1.90 BSC	
e	0.50 BSC	



SOLDERING FOOTPRINT*

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi soldering and mounting techniques reference manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98AON42381E**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**8 PIN FLIP−CHIP, 0.9X1.9, 0.5P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales